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## **FACSIMILE TRANSMITTAL**

Date: 5 March 2003

To: Examiner Hsien Ming Lee  
USPTO

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From: Kenneth D. Springer

Subject: Serial No.: 09/640,754  
Atty. Docket No.: SEC.747

No. of Pages (including cover): 11

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Comments:

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SEC.747

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re PATENT APPLICATION of:

In-sung KIM et al.

Group Art Unit: 2823

Serial No.: 09/640,754

Examiner: Hsien Ming LEE

Filed: 18 August 2000

SEMICONDUCTOR DEVICE  
HAVING SELF-ALIGNED  
CONTACT AND METHOD OF  
FABRICATING THE SAME

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**SUPPLEMENTAL AMENDMENT**

Honorable Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated 18 November 2002, and supplemental  
to the Amendment filed on 19 February 2003, please enter this Supplemental  
Amendment and amend the above-identified patent application as follows:

**IN THE SPECIFICATION:**

Please replace the paragraph beginning at page 4, line 22, with the following  
paragraphs:

-- FIG. 3A shows a cross-sectional view along an x-axis of a semiconductor  
substrate illustrating a step of a first embodiment of a semiconductor device  
fabrication method;